

Snubberless™, logic level and standard 8 A Triacs

Features

- Medium current Triac
- High static and dynamic commutation
- Low thermal resistance with clip bonding
- Packages is RoHS (2002/95/EC) compliant
- 600 V V_{RM}

Applications

- Value sensitive application
- General purpose ac line load switching
- Motor control circuits in power tools
- Small home appliances, lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

Description

Available in through-hole, the T8T series of Triacs can be used as on/off or phase angle control function in general purpose ac switching where high commutation capability is required.

This series can be designed-in in many value sensitive appliances thanks to the parameters guidance provided in the following pages.

Provides insulation rated at 2500 V rms (TO-220AB insulated package).

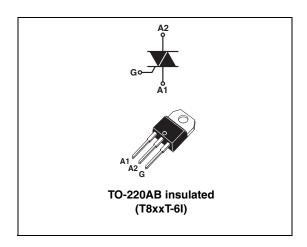


Table 1. Device summary

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Order code	Symbol	Value			
T810T-6I	I _{GT} 3Q logic level	10 mA			
T820T-6I T835T-6I	I _{GT} 3Q Snubberless	20 / 35 mA			
T825T-6I	I _{GT} 4Q standard	25 mA			

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Characteristics T8T

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Table 2. Absolute ratings (limiting values; $T_j = 25$ °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
I _{T(RMS)}	On-state rms current (full sine wave) $T_c = 97 ^{\circ}\text{C}$		8	Α	
1.	Non repetitive surge peak on-state current	F = 50 Hz	t _p = 20 ms	60	Α
ITSM	(full cycle, T _j initial = 25 °C)	F = 60 Hz	$t_p = 16.7 \text{ ms}$	63	А
l ² t	I ² t Value for fusing	I^2 t Value for fusing $t_p = 10 \text{ ms}$		26	A ² s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ $I_{r} \le 100 \text{ ns}$ $F = 60 \text{ Hz}$		T _j = 125 °C	50	A/µs
V _{DSM} / V _{RSM}	Non repetitive surge peak off-state voltage $t_p =$		T _j = 25 °C	V _{DRM} /V _{RRM} + 100	V
I _{GM}	Peak gate current $t_p = 20 \ \mu s$ $T_j = 125 \ ^{\circ}C$		4	Α	
P _{G(AV)}	Average gate power dissipation $T_j = 125$ °C			1	W
T _{stg}	Storage junction temperature range			- 40 to + 150	°C
T _j	Operating junction temperature range			- 40 to + 125	°C



T8T Characteristics

Table 3. Electrical characteristics (T_j = 25 °C, unless otherwise specified)

Cumhal	Test conditions	Overdwent		T8xxT			Unit	
Symbol	rest conditions	Quadrant		T810T	T820T	T825T	T835T	Offic
. (1)	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	MAX.	10	20	25	35	mA
I _{GT} ⁽¹⁾		IV				40		
V _{GT}	$V_D = V_{DRM}, R_L = 30 \Omega,$ $T_j = 25 ^{\circ}C$	ALL	MAX.	1.3		V		
V _{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$, $T_j = 125 \text{ °C}$	ALL	MIN.	0.2		V		
I _H ⁽²⁾	I _T = 500 mA	-	MAX.	15	25	30	40	mA
	I _G = 1.2 I _{GT}	I - III		20	35	40	50	
IL		IV	MAX.			40		mA
		II		25	40	70	70	
dV/dt (2)	V _D = 67% V _{DRM,} gate open	T _j = 125 °C	MIN.	100	750	500	2000	V/µs
uv/ut · /		$T_j = 150 {}^{\circ}C^{(3)}$	IVIIIN.	50	500	300	1000	v/µS
	(dV/dt)c = 0.1 V/μs			5.4				
	(dV/dt)c = 10 V/μs	T _j = 125 °C		2		4.5		
(di/dt)c (2)	Without snubber		MIN.		3.4		8	A/ms
(ui/ut)C · /	(dV/dt)c = 0.1 V/μs		IVIIIN.	2.5				AVIIIS
	(dV/dt)c = 10 V/μs	$T_j = 150 {}^{\circ}C^{(3)}$		1		2		
	Without snubber				2		6.5	

^{1.} Minimum I_{GT} is guaranted at 5% of I_{GT} max.

Table 4. Static characteristics

Symbol	Test conditions				Unit
V _T ⁽¹⁾	$I_{TM} = 11.3 \text{ A}, t_p = 380 \mu\text{s}$	T _j = 25 °C	MAX.	1.60	٧
V _{TO} (1)	Threshold voltage	T _j = 125 °C	MAX.	0.87	V
R _D ⁽¹⁾	Dynamic resistance	T _j = 125 °C	MAX.	60	mΩ
	V -V	T _j = 25 °C	MAX.	5	μΑ
ואוחם	$V_{\text{DRM}} = V_{\text{RRM}}$	T _j = 125 °C		1	mA
IRRM	$V_D = 0.9 \times V_{DRM}$	T _j = 150 °C ⁽²⁾	TYP.	1.9	

^{1.} For both polarities of A2 referenced to A1.

^{2.} For both polarities of A2 referenced to A1.

^{3.} Derating information for excess temperature above T_j max.

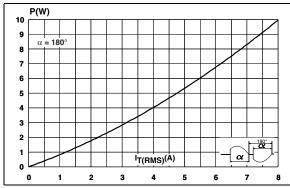
^{2.} Derating information for excess temperature above $T_j \, \text{max}$.

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Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	2.8	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case rms on-state current temperature



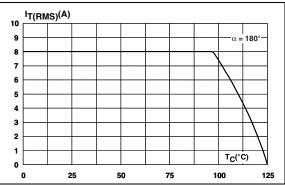
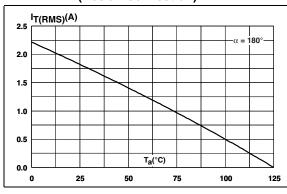


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration



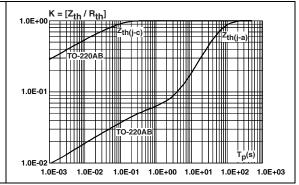
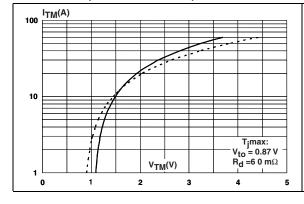
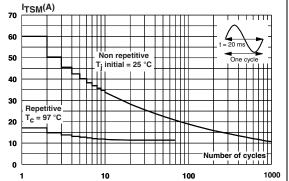


Figure 5. On-state characteristics (maximum values)

Figure 6. Surge peak on state current versus number of cycles





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Figure 7. Non repetitive surge peak on-state Figure 8. Relative variation of gate trigger current for a sinusoidal current and gate trigger voltage versus junction temperature

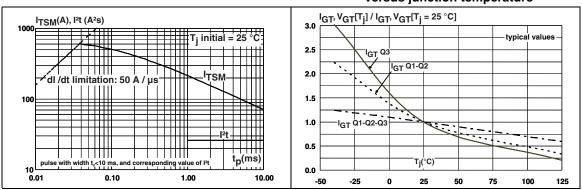


Figure 9. Relative variation of holding current and latching current versus junction temperature

Figure 10. Relative variation of static dV/dt immunity versus junction temperature

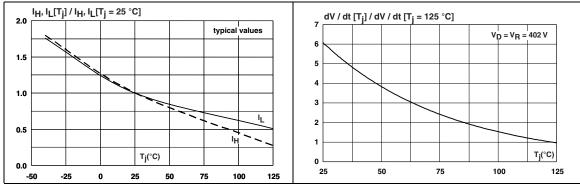
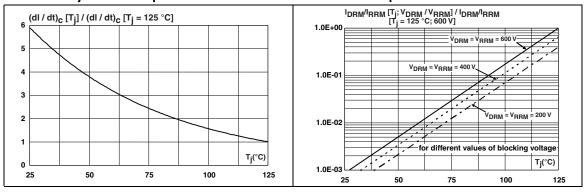


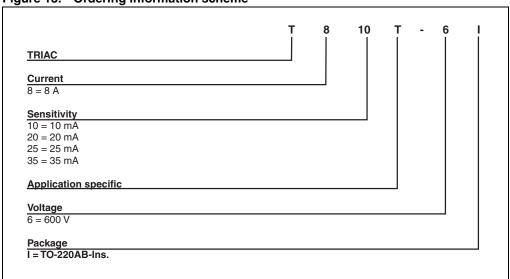
Figure 11. Relative variation of critical rate of Figure 12. Relative variation of leakage decrease of main current versus junction temperature

current versus junction temperature



2 Ordering information scheme

Figure 13. Ordering information scheme

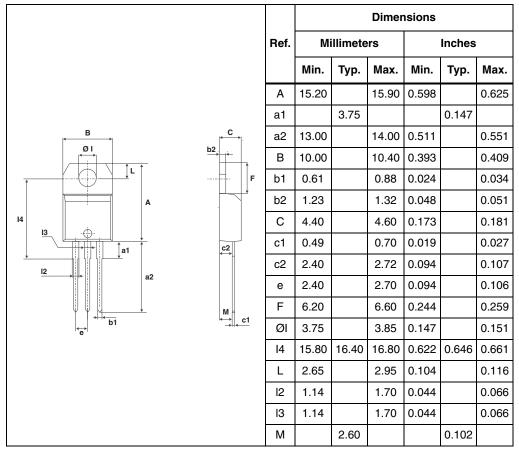


3 Package mechanical data

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-220AB Insulated dimensions



Ordering information T8T

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Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T810T-6I	T810T-6I				
T820T-6I	T820T-6I	TO-220AB-Ins.	2.3 g	50	Tube
T825T-6I	T825T-6I	10-220AB-IIIs.	2.5 g	50	Tube
T835T-6I	T835T-6I				

5 Revision history

Table 8. Document revision history

Date	Revision	Changes
10-Sep-2009	1	First issue.
18-Jan-2010	2	Updated pag.1.

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